SCBS142M - MAY 1992 - REVISED MARCH 2000

 Members of the Texas Instruments Widebus™ Family State of the Art Advanced BiGMOS 	SN74LVTH16244B DG	A WD PACKAGE GG, DGV, OR DL PACKAGE VIEW)
 State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power 	1 OE [1 1 Y1 [2	48 20E 47 1A1
 Dissipation Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 	1Y2 [] 3 GND [] 4 1Y3 [] 5	46 1A2 45 GND 44 1A3
 3.3-V V_{CC}) Support Unregulated Battery Operation 	1Y4 🕻 6	43 1A3 43 1A4 42 V _{CC}
Down to 2.7 V	V _{CC} [7 2Y1 [8	41 2A1
 Typical V_{OLP} (Output Ground Bounce) <0.8 V at V_{CC} = 3.3 V, T_A = 25°C 	2Y2 9 GND 10	39 GND
 I_{off} and Power-Up 3-State Support Hot Insertion 	2Y3 11 2Y4 12	37 2A4
 Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown 	3Y1 [13 3Y2 [14 GND [15	35 3A2
ResistorsLatch-Up Performance Exceeds 100 mA Per	3Y3 [16 3Y4 [17	33 3 A3
 JESD 78, Class II ESD Protection Exceeds JESD 22 	V _{CC} [18 4Y1 [19	31 🛛 V _{CC}
 2000-V Human-Body Model (A114-A) 200-V Machine Model (A115-A) 	4Y2 20 GND 21	29 4A2
 – 1000-V Charged-Device Model (C101) Package Options Include Plastic Shrink 	4Y3 [22 4Y4 [23	27 4 A3
Small-Outline (DL), Thin Shrink	4 0E [24	25 30E

Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

description

The SN54LVTH16244A and SN74LVTH16244B devices are 16-bit buffers and line drivers designed for low-voltage (3.3-V) V_{CC} operation, but with the capability to provide a TTL interface to a 5-V system environment. These devices can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer. These devices provide true outputs and symmetrical active-low output-enable (\overline{OE}) inputs.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

When V_{CC} is between 0 and 1.5-V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5-V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

These devices are fully specified for hot-insertion applications using I_{off} and power-up 3-state. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.



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SCBS142M - MAY 1992 - REVISED MARCH 2000

description (continued)

The SN54LVTH16244A is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74LVTH16244B is characterized for operation from -40°C to 85°C.

FUNCTION TABLE (each 4-bit buffer)

INP	UTS	OUTPUT							
OE	Α	Y							
L	Н	Н							
L	L	L							
Н	Х	Z							

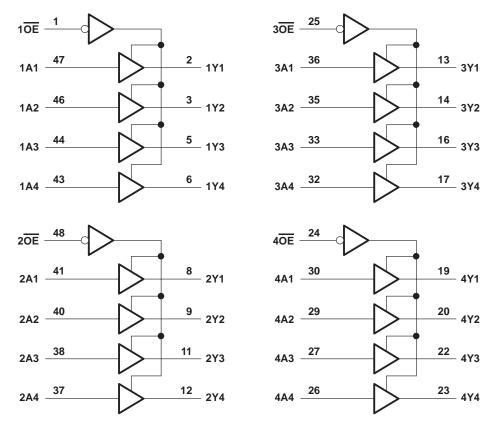
logic symbol[†]

10E 20E 30E 40E	1 48 25 24 24	EN1 EN2 EN3 EN4				
1A1	47		1		2	1Y1
1A2	46			1 V	3	1Y2
1A3	44				5	1Y3
1A3	43				6	1Y4
2A1	41		1	2 ▽	8	2Y1
2A1 2A2	40		1	2 *	9	211 2Y2
2A2 2A3	38				11	2Y3
2A3 2A4	37	<u> </u>			12	213 2Y4
2A4 3A1	36		4	3 ▽	13	
3A2	35	<u> </u>	1	3 V	14	3Y1
	33	<u> </u>			16	3Y2
3A3	32	┣───			17	3Y3
3A4	30	┣──	4	4 ▽	19	3Y4
4A1	29		1	4 ∨	20	4Y1
4A2	27				22	4Y2
4A3	26	 			23	4Y3
4A4						4Y4

[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high-impedance	
or power-off state, V _O (see Note 1)	–0.5 V to 7 V
Voltage range applied to any output in the high state, V _O (see Note 1)	0.5 V to V _{CC} + 0.5 V
Current into any output in the low state, I _O : SN54LVTH16244A	
SN74LVTH16244B	
Current into any output in the high state, I _O (see Note 2): SN54LVTH16244A	48 mA
SN74LVTH16244B	64 mA
Input clamp current, I _{IK} (V _I < 0)	–50 mA
Output clamp current, I_{OK} (V _O < 0)	
Package thermal impedance, θ_{IA} (see Note 3): DGG package	
DGV package	
DL package	
Storage temperature range, T _{stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This current flows only when the output is in the high state and $V_O > V_{CC}$.

3. The package thermal impedance is calculated in accordance with JESD 51.



SCBS142M - MAY 1992 - REVISED MARCH 2000

recommended operating conditions (see Note 4)

			SN54LVTH	16244A	SN74LVTH	UNIT	
			MIN	MAX	MIN	MAX	UNIT
VCC	Supply voltage	2.7	3.6	2.7	3.6	V	
VIH	High-level input voltage	2		2		V	
VIL	Low-level input voltage		0.8		0.8	V	
VI	Input voltage		5.5		5.5	V	
ЮН	High-level output current			-24		-32	mA
IOL	Low-level output current			48		64	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
Δt/ΔV _{CC}	Power-up ramp rate		200		200		μs/V
ТА	Operating free-air temperature	-55	125	-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



SCBS142M - MAY 1992 - REVISED MARCH 2000

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			SN54LVTH16244A			SN74LVTH16244B				
FAI	RAINETER				түр†	MAX	MIN	түр†	MAX	UNIT		
V _{IK} V _{CC} = 2.7 V, I _I			lj = -18 mA			-1.2			-1.2	V		
		$V_{CC} = 2.7 V \text{ to } 3.6 V,$	I _{OH} = -100 μA	V _{CC} –0.	.2		V _{CC} -0.	2				
Varia		V _{CC} = 2.7 V,	I _{OH} = -8 mA	2.4			2.4			v		
VOH		V _{CC} = 3 V	I _{OH} = -24 mA	2								
		vCC = 2 v	I _{OH} = -32 mA				2					
		Vec - 27V	I _{OL} = 100 μA			0.2			0.2			
		$V_{CC} = 2.7 V$	I _{OL} = 24 mA			0.5			0.5			
Max			I _{OL} = 16 mA			0.4			0.4	v		
VOL			I _{OL} = 32 mA			0.5			0.5	V		
		$V_{CC} = 3 V$	I _{OL} = 48 mA			0.55						
			I _{OL} = 64 mA						0.55			
		V _{CC} = 0 or 3.6 V,	V _I = 5.5 V			50			10			
	Control inputs	V _{CC} = 3.6 V,	$V_I = V_{CC} \text{ or } GND$			±1			±1	1		
II	Data inputs	V _{CC} = 3.6 V	Al = ACC			1			1	μA		
			V _I = 0			-5			-5			
loff		$V_{CC} = 0,$	V_{I} or V_{O} = 0 to 4.5 V	= 0 to 4.5 V ±100		±100	μΑ					
		V _{CC} = 3 V	V _I = 0.8 V	75			75			μΑ		
ll(hold)	Data inputs		V _I = 2 V	-75			-75					
. ,		V _{CC} = 3.6 V [‡] ,	V _I = 0 to 3.6 V						±500			
IOZH		V _{CC} = 3.6 V,	V _O = 3 V			5			5	μA		
IOZL		V _{CC} = 3.6 V,	$V_{O} = 0.5 V$			-5			-5	μA		
IOZPU		$\frac{V_{CC}}{OE} = 0$ to 1.5 V, V _O = OE = don't care	= 0.5 V to 3 V,			±100*			±100	μΑ		
IOZPD		$\frac{V_{CC}}{OE}$ = 1.5 V to 0, V _O = OE = don't care	= 0.5 V to 3 V,			±100*			±100	μA		
		V _{CC} = 3.6 V,	Outputs high			0.19			0.19			
ICC		$I_{O} = 0,$	Outputs low		5		5		mA			
		$V_I = V_{CC}$ or GND	Outputs disabled			0.19			0.19	19		
ΔI_{CC} $V_{CC} = 3 V \text{ to } 3.6 V, \text{ One i}$ Other inputs at V_{CC} or G					0.2			0.2	mA			
Ci		VI = 3 V or 0			4			4		pF		
Co		V _O = 3 V or 0			9			9		pF		

*On products compliant to MIL-PRF-38535, this parameter is not production tested.

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$. [‡] This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.



SN54LVTH16244A, SN74LVTH16244B 3.3-V ABT 16-BIT BUFFERS/DRIVERS WITH 3-STATE OUTPUTS SCBS142M - MAY 1992 - REVISED MARCH 2000

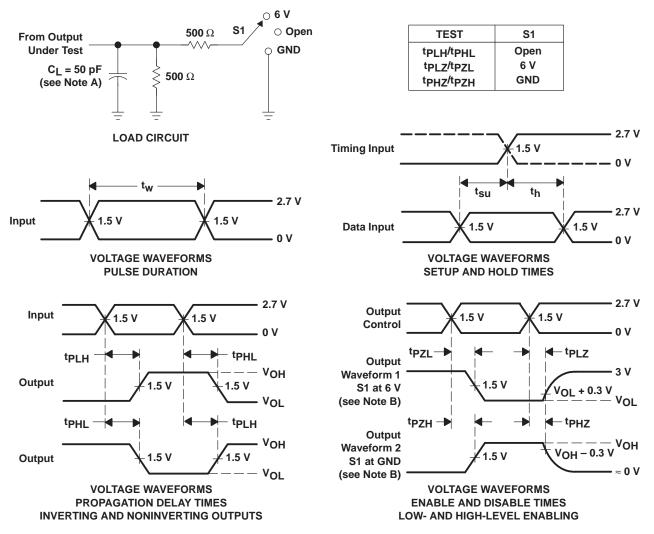
switching characteristics over recommended operating free-air temperature range, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

			S	SN54LVTH16244A			SN74LVTH16244B					
PARAMETER FROM (INPUT)		FROM TO (INPUT) (OUTPUT)		V _{CC} = 3.3 V ± 0.3 V V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V			V _{CC} = 2.7 V		UNIT	
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
^t PLH	А	v	1.1	4.4		4.6	1.2	2.3	3.2		3.7	ns
^t PHL	~	I	1.1	3.6		3.9	1.2	2	3.2		3.7	7
^t PZH	ŌĒ	v	1.1	4.6		5.4	1.2	2.6	4		5	ns
tPZL		Ι	1.1	5.4		6.2	1.2	2.7	4		5	115
^t PHZ	OE	V	1.6	5.7		6.2	2.2	3.3	4.5		5	ns
tPLZ	UE	1	1.2	5		4.7	2	3.1	4.2		4.4	115
^t sk(o)									0.5			ns

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.



SCBS142M - MAY 1992 - REVISED MARCH 2000



PARAMETER MEASUREMENT INFORMATION

NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_r \leq 2.5 ns, t_f \leq 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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